TOSHIBA PHOTOCOUPLER GaAlAs IRED & PHOTO IC

TLP2631

ISOLATED LINE RECEIVER

SIMPLEX / MULTIPLEX DATA TRANSMISSION

COMPUTER-PERIPHERAL INTERFACE

MICROPROCESSOR SYSTEM INTERFACE

DIGITAL ISOLATION FOR A/D, D/A CONVERSION

The TOSHIBA TLP2631 dual photocoupler consists of a pair of $GaA\ell As$ light emitting diode and integrated high gain, high speed photodetector.

This unit is 8-lead DIP.

The output of the detector circuit is an open collector, Schottky clamped transistor.

A Faraday shield integrated on the photodetector chip reduces the effects of capacitive coupling between the input LED emitter and the high gain stages of the detector. This provides an effective common mode transient immunity of $1000 \text{V}/\mu\text{s}$.

Weight: 0.54g

- Input Current Threshold: IF=5mA (MAX.)
- Switching Speed : 10MBd (TYP.)
- Common Mode Transient Immunity

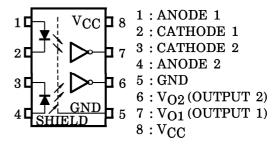
: $\pm 1000 \text{V} / \mu \text{s}$ (MIN.)

• Guaranteed Performance Over Temperature : 0~70°C

• Isolation Voltage : 2500V_{rms} (MIN.)

• UL Recognized : UL1577, File No. E67349

PIN CONFIGURATION (TOP VIEW)

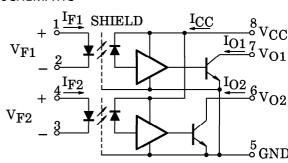


TRUTH TABLE (Positive Logic)

INPUT	OUTPUT
Н	L
L	Н

A 0.01 to $0.1\mu F$ bypass capacitor must connected between pins 8 and 5 (See Note 1).

SCHEMATIC



2001-09-27

MAXIMUM RATINGS (No derating required up to 70°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT
	Foward Current (Each Channel)	$I_{\mathbf{F}}$	20	mA
LED	Pulse Forward Current (Each Channel)*	$I_{ extbf{FP}}$	30	mA
	Reverse Voltage (Each Channel)	$v_{\mathbf{R}}$	5	V
	Output Current (Each Channel)	I_{O}	16	mA
OR	Output Voltage (Each Channel)	v_{O}	-0.5~7	V
DETECTOR	Supply Voltage (1 Minute Maximum)	v_{CC}	9C 7	
DE	Output Collector Power Dissipation (Each Channel)	PO	40	mW
Operating Temperature Range		$\mathrm{T_{stg}}$	-55~125	°C
St	orage Temperature Range	$\mathrm{T}_{\mathrm{opr}}$	-40~85	°C
Lead Soldering Temperature (10s)**		$T_{ m sol}$	260	°C
Isolation Voltage (AC, 1min., R.H.≤60%, Note 3)		BV _S 2500		Vrms

^{*} $t \le 1$ msec Duration.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input Current, Low Level, Each Channel	I_{FL}	0	_	250	μ A
Input Current, High Level, Each Channel	I_{FH}	6.3*		20	mA
Supply Voltage, Output	v_{CC}	4.5	5	5.5	V
Fan Out (TTL Load, Each Channel)	N	_	_	8	
Operating Temperature	$T_{ m opr}$	0	_	70	°C

^{* 6.3}mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0mA or less.

^{** 2}mm below seating plane.

ELECTRICAL CHARACTERISTICS (Ta = $0 \sim 70^{\circ}$ C, Unless otherwise noted)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.*	MAX.	UNIT
Input Forward Voltage (Each Channel)	$ m V_{ m F}$	I _F =10mA, Ta=25°C	_	1.65	1.75	V
Input Diode Temperature Coefficient (Each Channel)	ΔV _F /ΔTa	I _F =10mA	_	-2.0	1	mV/°C
Input Reverse Breakdown Voltage (Each Channel)	$BV_{\mathbf{R}}$	I _R =10μA, Ta=25°C	5	_	-	V
Input Capacitance (Each Channel)	C_{T}	$V_{ m F}$ =0, f=1MHz	_	45	1	pF
High Level Output Current (Each Channel)	IOH	$V_{CC} = 5.5V, V_{O} = 5.5V$ $I_{F} = 250 \mu A$	_	1	250	μ A
Low Level Output Voltage (Each Channel)	v_{OL}	V _{CC} =5.5V, I _F =5mA I _{OL} (Sinking) =13mA	_	0.4	0.6	V
High Level Supply Current (Both Channels)	ICCH	$V_{\rm CC} = 5.5 V, I_{\rm F} = 0$	_	14	30	mA
Low Level Supply Current (Both Channels)	I_{CCL}	$V_{\rm CC} = 5.5 \text{V}, \ I_{\rm F} = 10 \text{mA}$	_	24	38	mA
Isolation Voltage	$R_{\mathbf{S}}$	$V_S = 500V, R.H. \le 60\%$ (Note 3)	5×10^{10}	10^{14}	_	Ω
Capacitance (Input-Output)	c_{S}	f=1MHz (Note 3)	_	0.6	_	pF
Input-Input Leakage Current	I_{I-I}	R.H. \leq 60%, t=5s V _{I-I} =500V (Note 6)	_	0.005	_	μ A
Resistance (Input-Input)	R_{I-I}	V _{I-I} =500V (Note 6)	_	1011	_	Ω
Capacitance (Input-Input)	c_{I-I}	f=1MHz (Note 6)	_	0.25	_	pF

^{*} All typical values are at $V_{\rm CC} = 5V$, $Ta = 25 ^{\circ}C$.

SWITCHING	CHARACTERISTICS	$(Ta = 25^{\circ}C,$	$V_{CC} = 5V$
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CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Propagation Delay Time to Low Output Level	$t_{ m pHL}$	1	$I_F=0 \rightarrow 7.5 \text{mA}, R_L=350\Omega$ $C_L=15 \text{pF} \text{ (Each Channel)}$	_	60	75	ns
Propagation Delay Time to High Output Level	t_{pLH}	1	I_F =7.5mA \rightarrow 0, R_L =350 Ω C_L =15pF (Each Channel)	_	60	75	ns
Output Rise time, Output Fall time (10~90%)	t _r , t _f	1	$I_F = 0 \rightleftharpoons 7.5 \text{mA}, R_L = 350 \Omega$ $C_L = 15 \text{pF} \text{ (Each Channel)}$	_	30	_	ns
Common Mode Transient Immunity at High Output Level	CM_{H}	2	$I_F=0, R_L=350\Omega$ $V_{CM}=400V,$ $V_{O} (MIN.)=2V$ (Each Channel, Note 4)	1000	10000	_	V/μs
Common Mode Transient Immunity at Low Output Level	CM_{L}	2	$I_F = 7.5 \text{mA}, R_L = 350 \Omega$ $V_{CM} = 400 V$ $V_{O} \text{ (MAX.)} = 0.8 V$ (Each Channel, Note 5)	-1000	-10000	_	V/μs

- (Note 1) 2mm below seating plane
- (Note 2) The V_{CC} supply voltage to each TLP2631 isolator must be bypassed by a $0.01\mu F$ capacitor or larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to the package V_{CC} and GND pins each device.
- (Note 3) Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and Pins 5, 6, 7 and 8 shorted together.
- (Note 4) CM $_{\rm H}$ ·The maximum tolerable rate of rise of the common mode voltage to ensure the output will remain in the high state (i.e., $V_{\rm OUT}{>}2.0V$). Measured in volts per microsecond (V/ μ s).

Volts/microsecond can be translated to sinusoidial voltages:

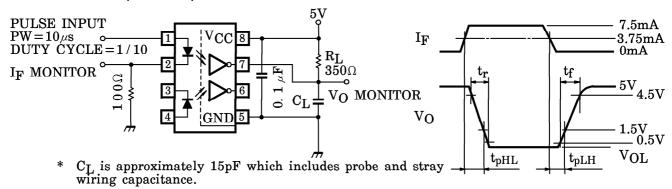
$$V/\mu s = \frac{(dVCM)}{dt}$$
 Max.= f_{CM} V_{CM} (p.p.)

Example:

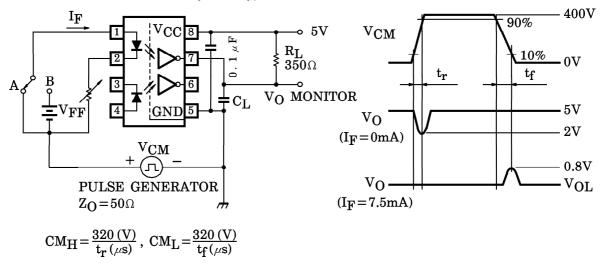
 V_{CM} =319Vpp when f_{CM} =1MHz using CML and CMH=1000V/ μ s data sheet specified minimum.

- (Note 5) $\overline{\text{CM}_L}$. The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state (i.e., $V_{\text{OUT}} > 0.8V$). Measured in volts per microsecond (V/ μ s).
- (Note 6) Measured between pins 1 and 2 shorted together, and pins 3 and 4 shorted together.

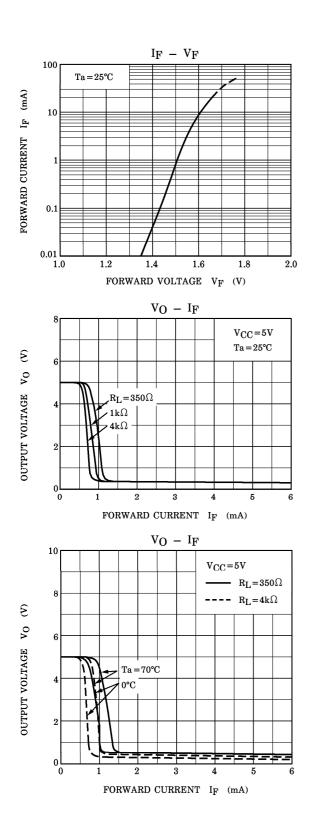
TEST CIRCUIT 1. t_{pHL} and t_{pLH}

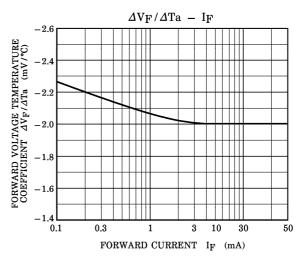


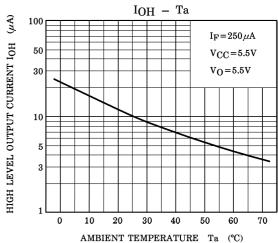
TEST CIRCUIT 2. Transient Immunity and Typical Waveforms.

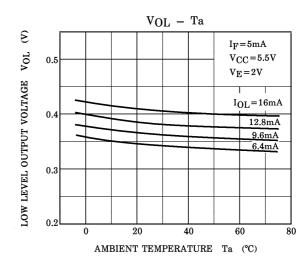


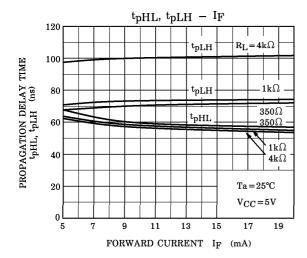
* $C_{\rm L}$ is approximately 15pF which includes probe and stray wiring capacitance.

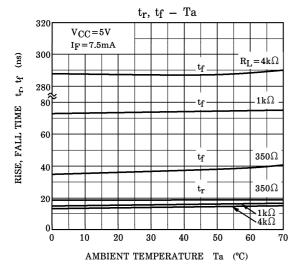


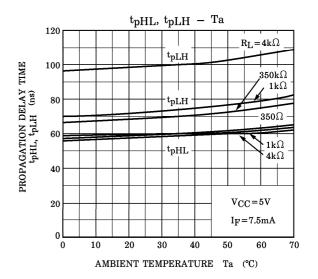












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